

SANYO	No.3026	2SA1706/2SC4486
		PNP/NPN Epitaxial Planar Silicon Transistors High-Current Switching Applications

Applications

- Voltage regulators, relay drivers, lamp drivers.

Features

- Adoption of FBET, MBIT processes.
- Large current capacity and wide ASO.
- Low collector-to-emitter saturation voltage.
- Fast switching speed.

() : 2SA1706

Absolute Maximum Ratings at Ta = 25°C

			unit
Collector to Base Voltage	V _{CBO}	(-)60	V
Collector to Emitter Voltage	V _{CEO}	(-)50	V
Emitter to Base Voltage	V _{EBO}	(-)6	V
Collector Current	I _C	(-)2	A
Collector Current(Pulse)	I _{CP}	(-)4	A
Collector Dissipation	P _C	1	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

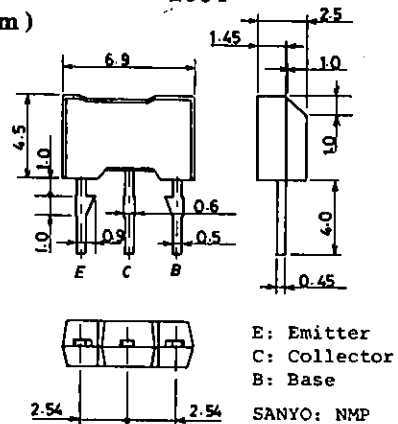
			min	typ	max	unit
Collector Cutoff Current	I _{CBO}	V _{CB} = (-)50V, I _E = 0			(-)100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} = (-)4V, I _C = 0			(-)100	nA
DC Current Gain	h _{FE} (1)	V _{CE} = (-)2V, I _C = (-)100mA	100*		400*	
			40			
Gain-Bandwidth Product	f _T	V _{CE} = (-)10V, I _C = (-)50mA		150		MHz
C-E Saturation Voltage	V _{CE(sat)}	I _C = (-)1A, I _B = (-)50mA	(-0.3)0.15		(-0.7)0.4	V
B-E Saturation Voltage	V _{BE(sat)}	I _C = (-)1A, I _B = (-)50mA	(-)0.9		(-)1.2	V
Output Capacitance	c _{ob}	V _{CB} = (-)10V, f = 1MHz	(22)12			pF

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※ : The 2SA1706/2SC4486 are classified by 100mA h_{FE} as follows :

100 R 200	140 S 280	200 T 400
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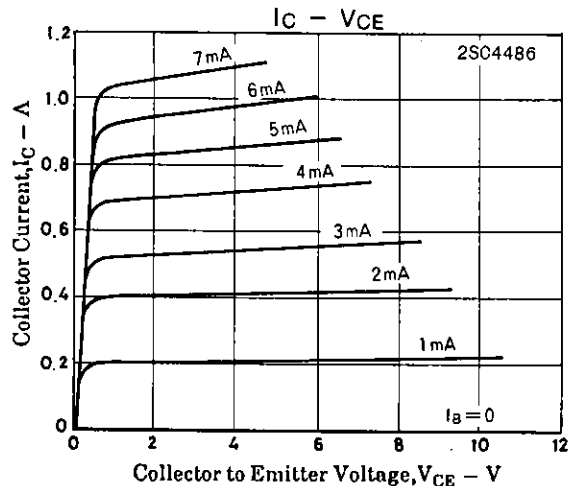
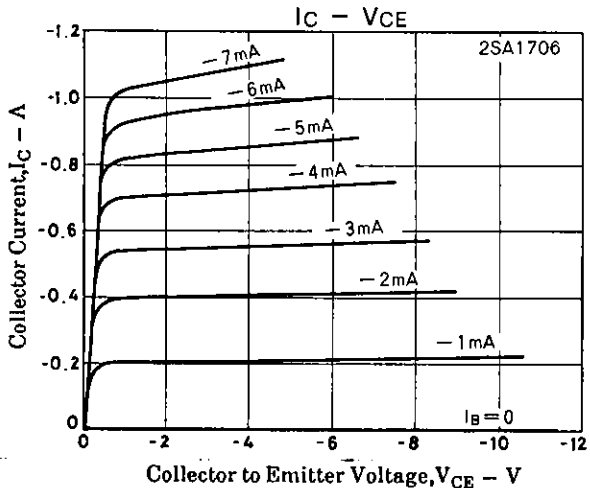
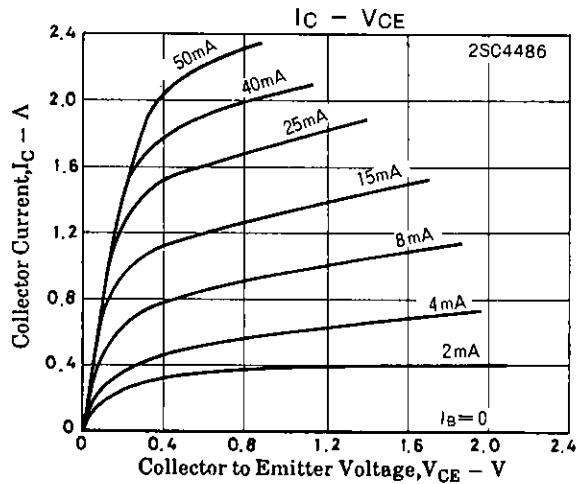
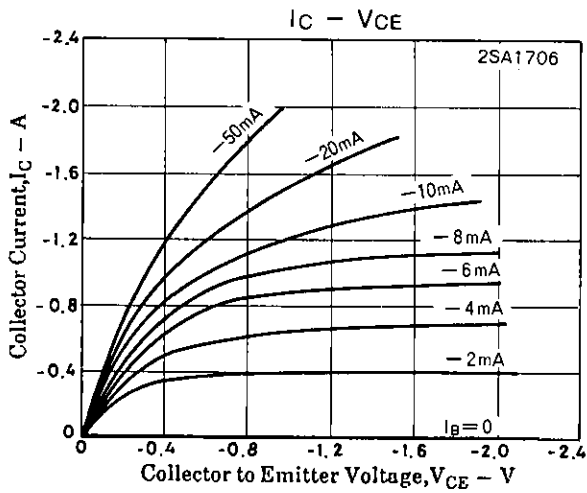
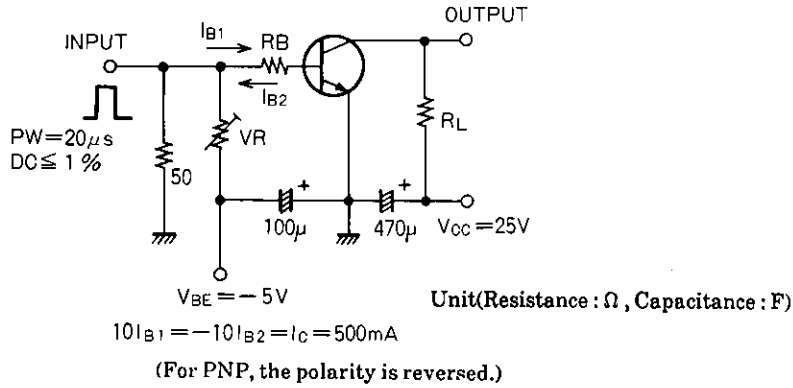
Package Dimensions 2064
(unit: mm)



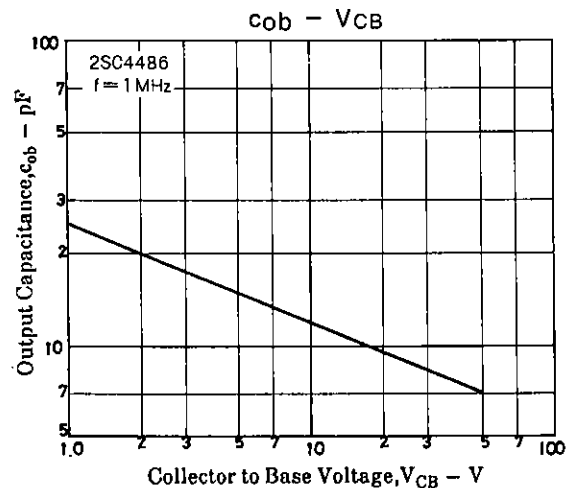
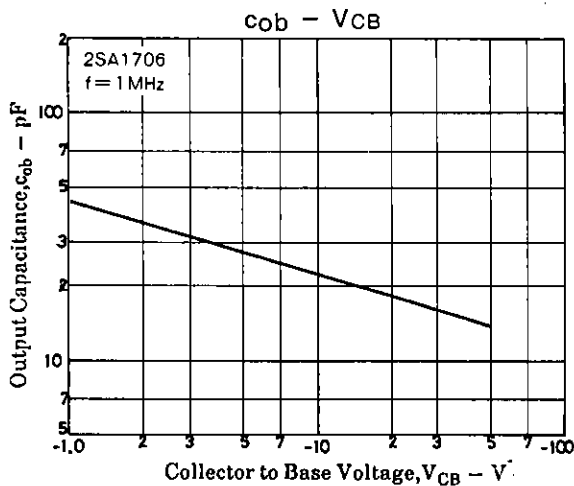
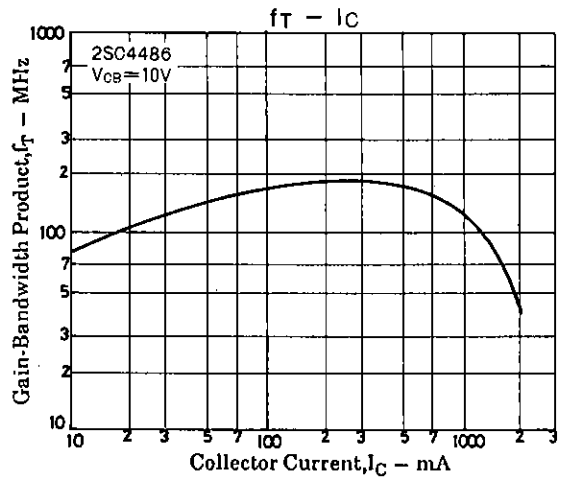
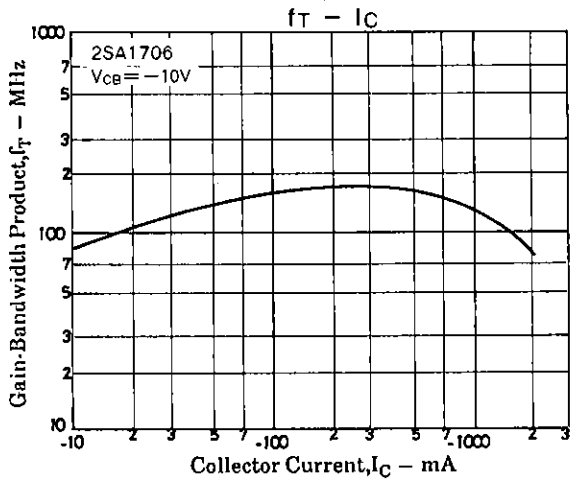
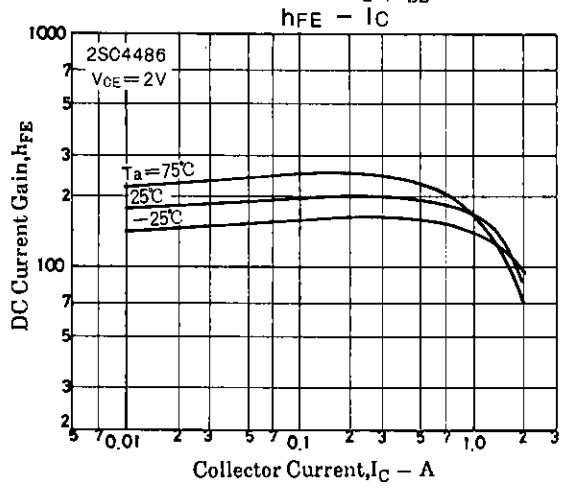
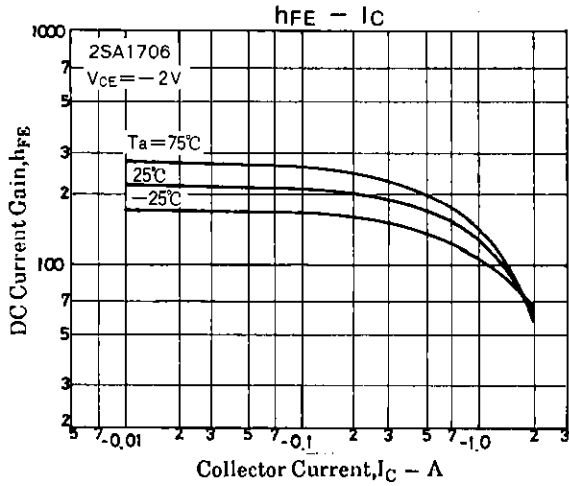
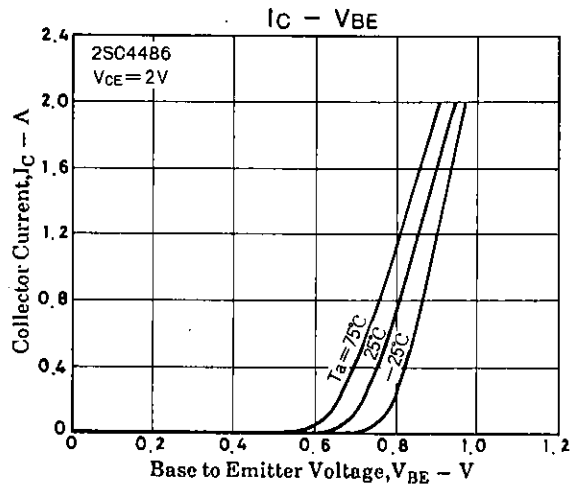
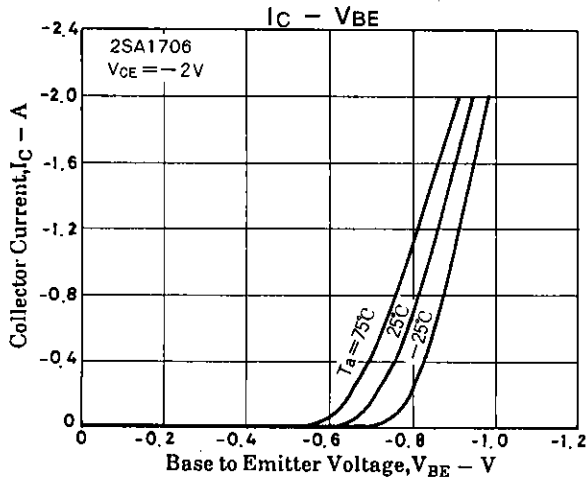
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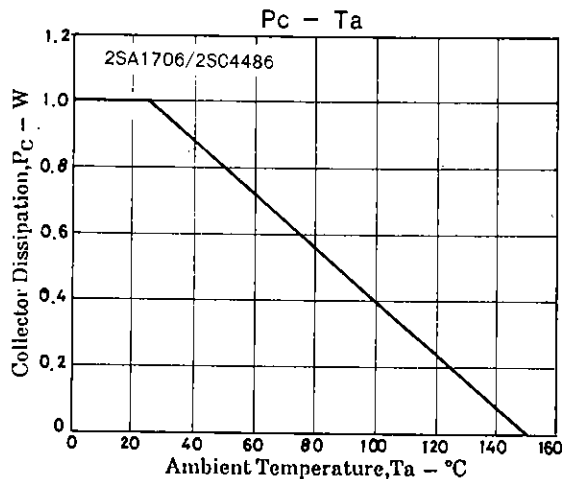
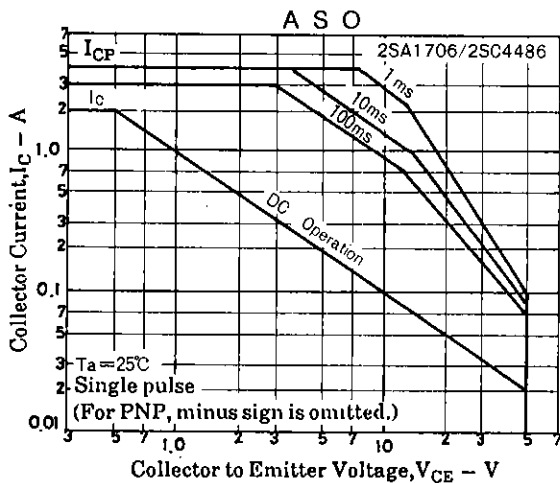
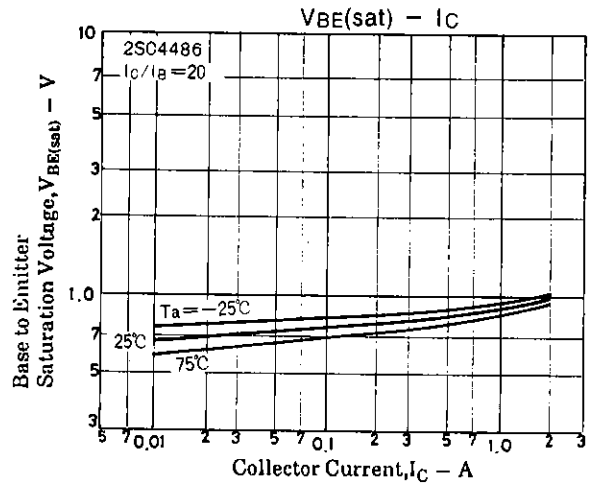
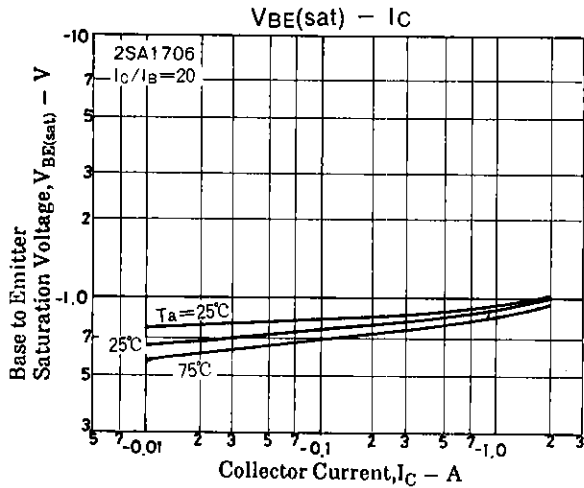
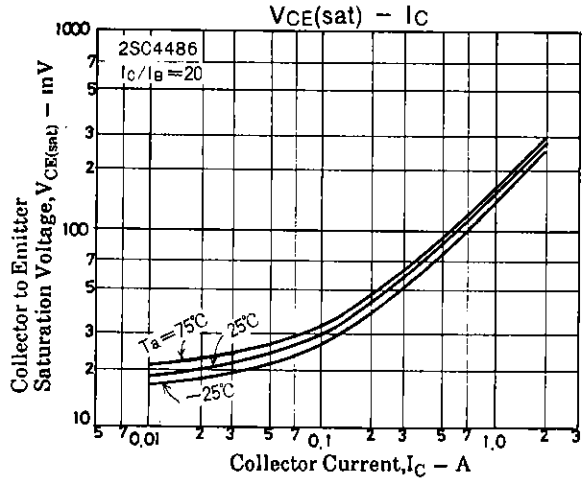
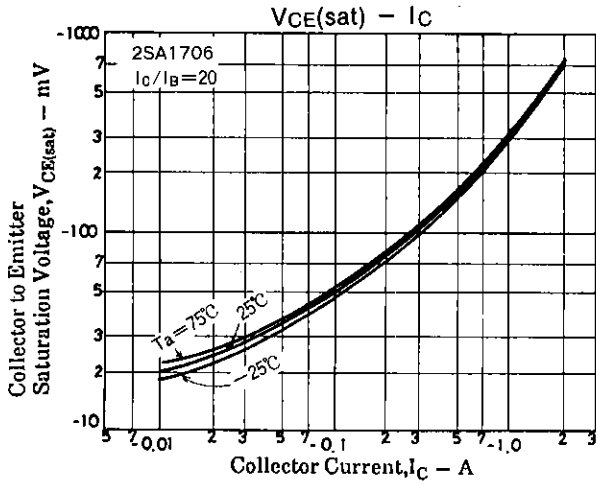
			min	typ	max	unit
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)50			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-)6			V
Turn-ON Time	t_{on}	See specified Test Circuit.		60		ns
Storage Time	t_{stg}	∕	(450)550			ns
Fall Time	t_f	∕		30		ns

Switching Time Test Circuit



2SA1706/2SC4486





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